



# FC106

NPN Epitaxial Planar Silicon Composite Transistor

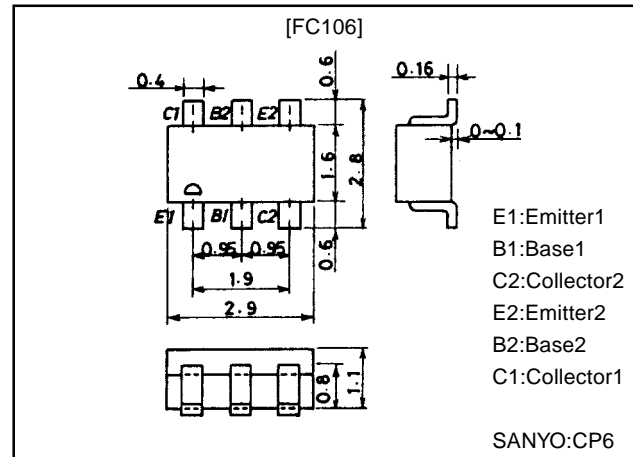
## Switching Applications

### Features

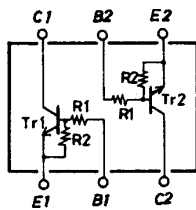
- On-chip bias resistors ( $R_1=47k\Omega$ ,  $R_2=47k\Omega$ )
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC106 is formed with two chips, being equivalent to the 2SC3395, placed in one package.
- Excellent in thermal equilibrium and pair capability.

### Package Dimensions

unit:mm  
2067



### Electrical Connection



### Specifications

#### Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CBO}$		50	V
Collector-to-Emitter Voltage	$V_{CEO}$		50	V
Emitter-to-Base Voltage	$V_{EBO}$		10	V
Collector Current	$I_C$		100	mA
Collector Current (Pulse)	$I_{CP}$		200	mA
Collector Dissipation	$P_C$	1unit	200	mW
Total Dissipation	$P_T$		300	mW
Junction Temperature	$T_J$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to+150	$^\circ\text{C}$

#### Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.1	$\mu\text{A}$
Collector Cutoff Current	$I_{CEO}$	$V_{CE}=40V, I_B=0$			0.5	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$	30	53	80	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=5\text{mA}$	50			
Gain-Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=5\text{mA}$		250		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1\text{MHz}$		3.3		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=5\text{mA}, I_B=0.25\text{mA}$		0.1	0.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	50			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=100\mu\text{A}, R_{BE}=\infty$	50			V
Input OFF-State Voltage	$V_{I(off)}$	$V_{CE}=5V, I_C=100\mu\text{A}$	0.8	1.1	1.5	V
Input ON-State Voltage	$V_{I(on)}$	$V_{CE}=0.2V, I_C=5\text{mA}$	1.0	2.5	5.0	V
Input Resistance	$R_1$		32	47	62	$k\Omega$
Resistance Ratio	$R_1/R_2$		0.9	1.0	1.1	

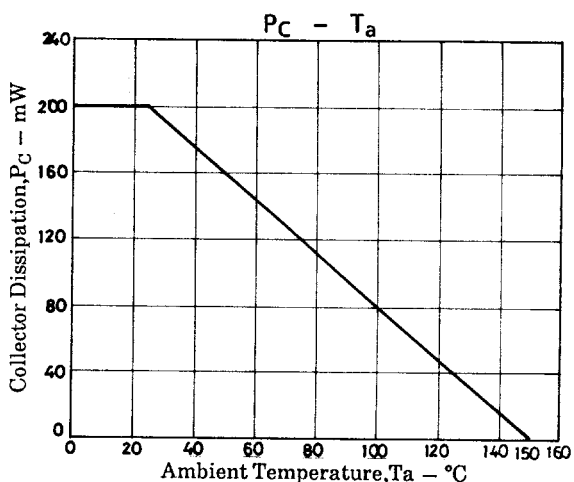
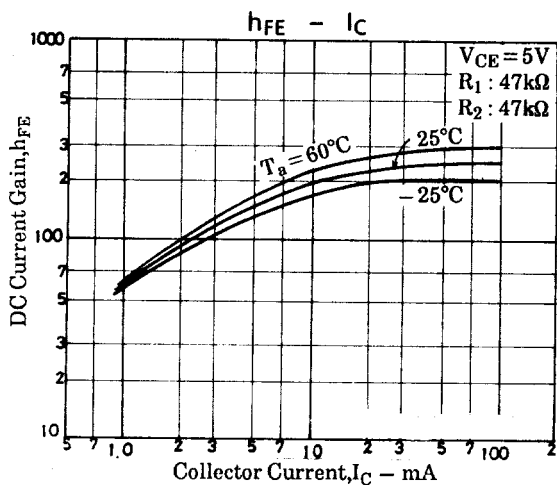
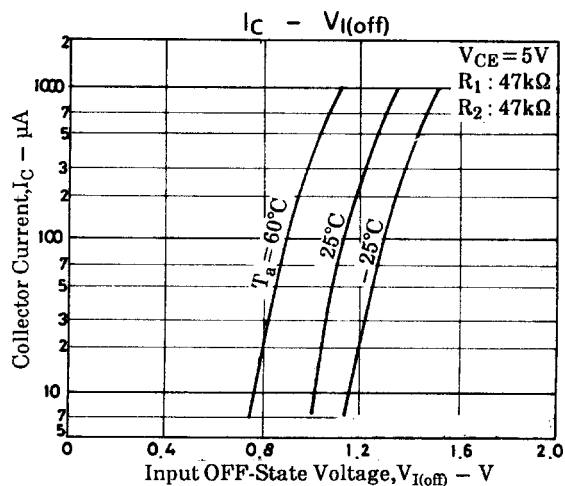
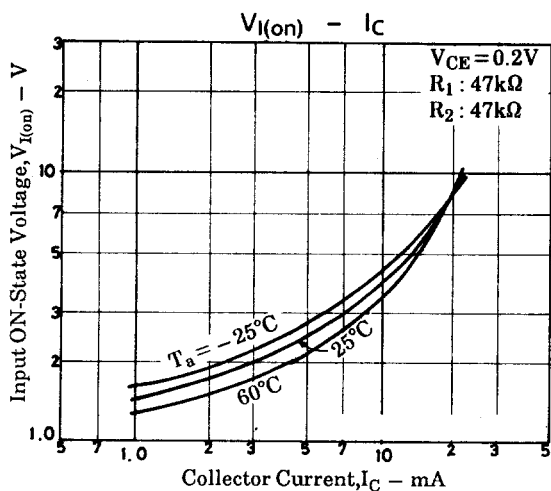
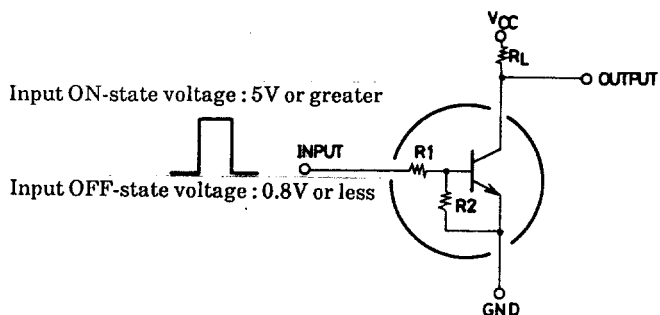
Note: The specifications shown above are for each individual transistor.

Marking:106

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Sample Application Circuit



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